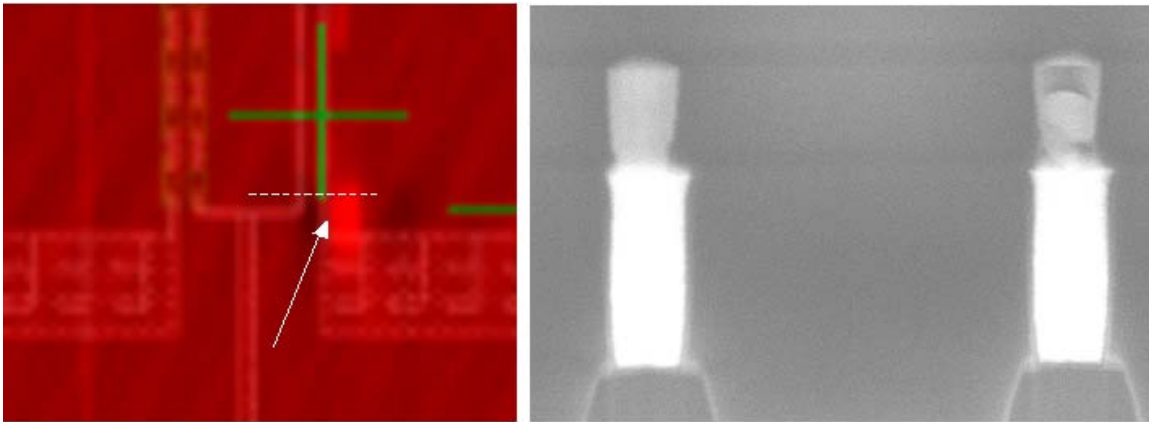


High Resistance SEI Topside 8" Wafer



Left: SEI signal overlaid with contact chain structure.
Right: Cross-sectional SEM image (at dotted line) of disrupted metal trace above contact.
Isolation accuracy in this case was within one contact on the chain. Images and data obtained with the Infrascan 200, courtesy of a customer.

Resistance $R > 1 \text{ M}\Omega$
Laser power approximately 20mW at 1340nm.
Voltage amplification mode
SEI (Seebeck effect) no current bias.